


REMARKS

In response to the election requirement in the Office Action of March 16, 2001, Applicants hereby elect without traverse the Group II claims - that is, claims 45-59, directed to a method of crystallizing a semiconductor film after exposing it to oxygen plasma. Applicants have amended claim 52 and new claims 60-66 have been added.

Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

52. (Amended) A method for manufacturing a semiconductor device comprising steps of:

contacting a material for promoting crystallization to at least a part of an initial semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma; and

crystallizing said initial semiconductor film using said material, to obtain a crystalline semiconductor film.